

APPENDIX A

Japanese patent application publication No. 56126916A by Akira: this published application generally relates to, inter alia, diffusing selenium with high accuracy into a chalcogenide with silver by use of photoresist and thermal treatment.

Additional Japanese patent documents are in Japanese. Application does not have an English translation. The relevance of these documents is not specifically known, but it is believed that they relate to technology having similarities to the technology of the application.

Abdel-All, et al., Vacuum 59 (2000) 845-853: published in December, this document generally relates to, inter alia, the electrical properties of $\text{Ge}_5\text{As}_{38}\text{Te}_{57}$ as a function of temperature.

*Adler and Moss, J. Vac. Sci. Technol. 9 (1972) 1182-1189: this document generally relates to, inter alia, two types of electrical/material switching – threshold and memory, in amorphous materials; the effects of temperature, pressure, and frequency on switching; and the physics of threshold voltage and memory.

Adler et al., Ref. Mod. Phys. 50 (1978) 209-220: this document generally relates to, inter alia, threshold switching in amorphous alloys, state (“on” and “off”) characteristics, and glass properties.

Afifi, et al., Appl. Phys. A 55 (1992) 167-169: this document generally relates to, inter alia, SeGe-Sb glasses.

*Afifi, et al., J. Phys. 17 (1986) 335-342: this document generally relates to, inter alia, electrical and thermal conductivity of $\text{Ge}_x\text{Se}_{1-x}$ compositions as a function of temperature. $\text{Ge}_{25}\text{Se}_{75}$ stoichiometry is disclosed.

Alekperova and Gadzhieva, 23 (1987) 137-139: this document generally relates to, inter alia, a characteristic diode state in Ag_2Se compositions upon heating (to 376-400°K).

*Aleksiejunas and Cesnys, Phys. Stat. Sol. (a) 19 (1973) K169-K171: this document generally relates to, inter alia, the subjects of selenium investigation and how $\text{Se-Ag}_2\text{Se}$ contributes silver ions to a selenium composition.

Angell, Annu. Rev. Phys. Chem. 43 (1992) 693-717: this document generally relates to, inter alia, the presence of ion conductors in solids.

Aniya, Solid State Ionics 136-137 (November 2,2000) 1085-1089: this document generally relates to, inter alia, ion conductor glasses.

Asahara and Izumitani, J. Non-Cryst. Solids 11 (1972) 97-104: this document generally relates to, inter alia, Cu-As-Se glass.

Asokan, et al., Phys. Rev. Lett. 62 (1989) 808-810: this document generally relates to, inter alia, $\text{Ge}_x\text{Se}_{100-x}$ glasses and their transition from semiconductor-like material to metal-like material.

*Axon Technologies Corp., *Technology Description: Programmable Metallization Cell*: this believed publication generally relates to, inter alia, use of chalcogenides doped with metal much as silver or copper to create solid state switch with lower voltage requirement.

Baranovskii and Cordes, J. Chem. Phys. 111 (1999) 7546-7557: this document generally relates to, inter alia, ionic glasses and conduction (percolation theory).

Belin et al., Sol. St. Ionics 136-137 (November 2,2000) 1025-1029: this document generally relates to, inter alia, conductivity spectra of the glass $0.5\text{Ag}_2\text{S}-0.5\text{GeS}_2$ and the temperature dependency of the conductivity.

Belin, et al., Solid State Ionics 143 (July 2, 2001) 445-455: this document generally relates to, inter alia, the electrical properties of $\text{Ag}_7\text{GeSe}_5\text{I}$ – an argyrodite compound.

Benmore and Salmon, Phys. Rev. Lett. 73 (1994) 264-267: this document generally relates to, inter alia, the characteristics of chalcogenide alloys.

Bernede, Thin Solid Films 70 (1980) L1-L4: this document is in the French language and the Applicant has no translation. It is presently understood to generally relate to, inter alia, metal- Ag_2Se -metal sandwich devices.

Bernede, Thin Solid Films 81 (1981) 155-160: this document generally relates to, inter alia, memories of selenium alloys with metal (e.g., Ag) electrodes, where the “on” memory states require constant voltage.

Bernede, Phys. Stat. Sol. (a) 57 (1980) K101-K104: this document generally relates to, inter alia, metal- Ag_2Se -P systems.

Bernede and Abachi, Thin Solid Films 131 (1985) L61-L64: this document generally relates to, inter alia, metal-insulator-metal thin films with electroforming effects; the films have silver, gold and copper electrodes.

*Bernede, et al., Thin Solid Films 97 (1982) 165-171: this document generally relates to, inter alia, Ag₂Se/Se/Metal thin film sandwiches, which were studied by shape of electrodes (e.g., symmetrical or asymmetrical).

Bernede, et al., Phys. Stat. Sol. (a) 74 (1982) 217-224: this document generally relates to, inter alia, switching in Al-Al₂O₃Ag_{2-x}Se_{1+x} devices.

Bondarev and Pikhitsa, Solid State Ionics 70/71 (1994) 72-76: this document generally relates to, inter alia, Ag⁽⁺⁾/RbAg₄I₅ boundary – depletion layer, and dendritic electrodeposition.

*Boolchand, Asian Journal of Physics (2000) 9, 709-72: this document generally relates to, inter alia, Ge_xSe_{1-x} glasses, which have selenium-rich and germanium-rich clusters, and the intrinsically-broken bond characteristics thereof.

*Boolchand and Bresser, Nature 410 (2001) 1070-1073: published April 26, this document generally relates to, inter alia, Ag₂Se as an electrolyte additive to glass, e.g., GeSe₄. Ge₃₀Se₇₀ glass was found not to work well because of Ag₂Se crystallization.

*Boolchand, et al., J. Optoelectronics and Advanced Materials, 3 (September 2001), 703: this document generally relates to, inter alia, a review of Raman tool scattering of chalcogenide glasses. The floppyness and rigidity is observed. Ge_xSe_{1-x} is disclosed, as is a stoichiometry of Ge₂₅Se₇₅.

*Boolchand, et al., Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132: this document generally relates to, inter alia, the prediction of glass rigidity in Ge_xSe_{1-x} glass, e.g., Ge₂₃Se₇₇.

*Boolchand, et al., Diffusion and Defect Data, Vol. 53-54 (1987) 415-420: this document generally relates to, inter alia, thermal annealing of $\text{Ge}_x\text{Se}_{1-x}$ films.

*Boolchand, et al., Phys. Rev. B 25 (1982) 2975-2978: this document generally relates to, inter alia, the examination of GeSe glass having Sn impurities by Mossbauer spectroscopy. Investigations into glass network topology, which has an intrinsically broken bond backbone, suggesting Ge and Se rich clusters.

Boolchand, et al., Sol. State Comm. 45 (1983) 183-185: this document generally relates to, inter alia, $\text{Ge}_x\text{Se}_{1-x}$ and $\text{Ge}_x\text{S}_{1-x}$ glasses.

*Boolchand and Bresser, Dep. Of ECECS, Univ. Cincinnati 45221-0030: this document generally relates to, inter alia, $\text{Ge}_x\text{Se}_{1-x}$ and the relation of glass transition temperature to Ge concentration in backbone. Although the publication date of this reference is not known to the Applicant, it was revised October 28, 1999 and is believed to be publicly available at the University of Cincinnati, Department of Electrical and Computer Engineering and Computer Science.

Boolchand and Grothaus, Eds. Chadi and Harrison, Proc. Int. Conf. Phys, Semicond., 17th (1985) 833-36: this document generally relates to, inter alia, GeSe and GeS glasses and the importance of a broken chemical order therein.

Bresser, et al., Phys. Rev. Lett. 56 (1986) 2493-2496: this document generally relates to, inter alia, an investigation of c- GeSe_2 structure.

Bresser, et al., J. de Physique 42 (1981) C4-193-C4-196: this document generally relates to, inter alia, the characteristics of GeSe_2 and GeS_2 glasses.

Bresser, et al., Hyperfine Interactions 27 (1986) 389-392: this document generally relates to, inter alia, germanium selenide glasses doped with tellurium.

Cahen, et al., Science 258 (1992) 271-274: this document generally relates to, inter alia, chalcopyrite CuInSe_2 glasses.

Chatterjee, et al., J. Phys. D: Appl. Phys. 27 (1994) 2624-2627: this document generally relates to, inter alia, $\text{As}_x\text{Te}_{100-x-y}\text{Se}_y$ glasses and the current, voltage, and electrical switching behavior. Discloses applicability in read mostly memories.

*Chen and Tai, Appl. Phys. Lett. 37 (1980) 1075-1077: this document generally relates to, inter alia, silver photodoping of $\text{Ge}_x\text{Se}_{1-x}$ and whisker formation (crystalline Ag_2Se).

Chen and Cheng, J. Am. Ceram. Soc. 82 (1999) 2934-2936: this document generally relates to, inter alia, germanium containing chalcogenides doped with Si_3N_4 .

Chen, et al., J. Non-Cryst. Solids 220 (1997) 249-253: this document generally relates to, inter alia, $\text{As}_{10}\text{Ge}_{30}\text{Se}_{60}$ glasses (and the like) doped with Si_3N_4 .

Cohen, et al., J. Non-Cryst. Solids 8-10 (1972) 885-891: this document generally relates to, inter alia, Ge-Te-X glasses as memory devices.

Croitoru, et al., J. Non-Cryst. Solids 8-10 (1972) 781-786: this document generally relates to, inter alia, the physics of conductivity in Ge-containing films.

Dalven and Gill, J. Appl. Phys. 38 (1967) 753-756: this document generally relates to, inter alia, beta- Ag_2Te .

Davis, Search 1 (1970) 152-155: this document generally relates to, inter alia, the subject of amorphous semiconductors as compared to glass.

*Dearnaley, et al., Rep. Prog. Phys. 33 (1970) 1129-1191: this document generally relates to, inter alia, background information about glass and memory.

*Dejus, et al., J. Non-Cryst. Solids 143 (1992) 162-180: this document generally relates to, inter alia, Ag-Ge-Se glass with Ag primarily bonded to Se. The reference discloses glass preparation.

den Boer, Appl. Phys. Lett. 40 (1982) 812-813: this document generally relates to, inter alia, a-Si:H sandwich structures and threshold switching from a low to high conductance.

Drusedau, et al., J. Non-Cryst. Solids 198-200 (1996) 829-832: this document generally relates to, inter alia, work with a-Si:H multilayers optoelectrical properties.

El Bouchairi, et al., Thin Solid Films 110 (1983) 107-113: this document generally relates to, inter alia, $\text{Ag}_{2-x}\text{Se}_{1+x}$ thin film electrical characteristics and metal-like conduction.

El Gharras, et al., J. Non-Cryst. Solids 155 (1993) 171-179: this document generally relates to, inter alia, photoconductivity of amorphous Se and Ge-Se alloy evaporated films, and reduction of photocurrent by increase of Ge content.

*El Ghrandi, et al., Thin Solid Films 218 (1992) 259-273: this document generally relates to, inter alia, GeSe films deposited by PECVD, Ag evaporation deposition onto glass and photodissolution into same, and optical properties are investigated. GeSe stoichiometries of 30/70 and 25/75, respectively, are disclosed.

*El Ghrandi, et al., Phys. Stat. Sol. (a) 123 (1991) 451-460: this document generally relates to, inter alia, dissolution of Ag into GeSe_{5.5} glass by flash evaporation.

El-kady, Indian J. Phys. 70 A (1996) 507-516: this document generally relates to, inter alia, Ge₂₁Se₁₇Te₆₂ glass and memory, switching, and current controlled negative resistance.

Elliott, J. Non-Cryst. Solids 130 (1991) 85-97: this document generally relates to, inter alia, mechanisms of photodissolution of metals (e.g., Ag) in chalcogenides based on ionic and electronic charge carriers.

*Elliott, J. Non-Cryst. Sol. 130 (1991) 1031-1034: this document generally relates to, inter alia, the photodissolution of metals (e.g, Ag) in chalcogenide glasses and the physics thereof.

Elsamanoudy, et al., Vacuum 46 (1995) 701-707: this document generally relates to, inter alia, studies of quaternary chalcogenide films with Te-As-Ge-Si sandwich structures between electrodes.

*El-Zahed and El-Korashy, Thin Solid Films 376 (November 1,2000) 236-240: this document generally relates to, inter alia, Ge₂₀Bi_xSe_{80-x} film analysis regarding conduction and changes from p to n type.

Fadel, Vacuum 44 (1993) 851-855: this document generally relates to, inter alia, a study of the switching and memory characteristics of Se₇₅Ge_{25-x}As_x films.

*Fadel and El-Shair, Vacuum 43 (1992) 253-257: this document generally relates to, inter alia, Se₇₅Ge₇Sb₁₈ glass electrical conduction and thermal character.

Feng, et al., Phys. Rev. Lett. 78 (1997) 4422-4425: this document generally relates to, inter alia, germanium selenide and germanium sulfide materials.

*Feng, et al., J. Non-Cryst. Solids 222 (1997) 137-143: this document generally relates to, inter alia, the structural character of $\text{Ge}_x\text{S}_{1-x}$ glass, e.g., hardness and elasticity.

*Fischer-Colbrie, et al., Phys. Rev. B 38 (1988) 12388-12403: this document generally relates to, inter alia, photodiffused Ag-GeSe₂ and the interaction between doped Ag with Se atoms and Ge with Ge atoms.

Fleury, et al., Phys. Stat. Sol. (a) 64 (1981) 311-316: this document generally relates to, inter alia, amorphous selenium films and their conductance.

Fritzsche, J. Non-Cryst. Sol. 6 (1971) 49-71: this document generally relates to, inter alia, background information on chalcogenides as semiconductors.

Fritzsche, Annual Review of Mat. Sci. 2 (1972) 697-744: this document generally relates to, inter alia, background information on amorphous semiconductors.

Gates, et al., J. Am. Chem. Soc. (2001): this document generally relates to, inter alia, creating Ag₂Se nanowires by chemical reaction.

Gosain, et al., Jap. J. Appl. Phys. 28 (1989) 1013-1018: this document generally relates to, inter alia, germanium telluride glasses sandwiched in electrodes and the physics thereof.

*Guin et al., J. Non-Cryst. Sol. 298 (March 28,2002) 260-269: this document generally relates to, inter alia, germanium selenide (GeSe) glass with low hardness, the

mechanical properties of which are investigated. Stoichiometries of the glass are disclosed as being, inter alia, 10/90, 20/80, and 30/70, respectively.

*Guin et al., J. Am. Ceram. Soc. 85 (June 2002) 1545-1552: this document generally relates to, inter alia, germanium selenide glasses and a study of the hardness properties thereof. Glass stoichiometries of 40/60 and 20/80, respectively, are disclosed.

Gupta, J. Non-Cryst. Sol. 3 (1970) 148-154: this document generally relates to, inter alia, switching in chalcogenides.

Haberland and Stiegler, J. Non-Cryst. Solids 8-10 (1972) 408-414: this document generally relates to, inter alia, glasses containing Te, As, Ge, and Si, and pulse sequence and time factors in switching.

Haifz, et al., J. Apply. Phys. 54 (1983) 1950-1954: this document generally relates to, inter alia, As-Se-Cu glasses.

Hajto, et al., Int. J. Electronics 73 (1992) 911-913: this document generally relates to, inter alia, metal/a-Si:H/metal devices.

Hajto, et al., J. Non-Cryst. Solids 266-269 (May 1,2000) 1058-1061: this document generally relates to, inter alia, a-Si:H ion conductors, polarity-dependant digital and analogue memory, and dependency on contact metals.

Hajto, et al., J. Non-Cryst. Solids 198-200 (1996) 825-828: this document generally relates to, inter alia, electroformed V/a-Si:H/Cr devices.

Hajto, et al., Phil. Mag. B 63 (1991) 349-369: this document generally relates to, inter alia, p+ type amorphous Si memory structures with polarity dependent analogue switching.

Hayashi, et al., Japan. J. Appl. Phys. 13 (1974) 1163-1164: this document generally relates to, inter alia, Au-CdS(CdSe)-Au systems and metal-Se-Sn-SnO₂ systems.

*Hegab, et al., Vacuum 45 (1994) 459-462: this document generally relates to, inter alia, Ge₂₀M₇₅Sb₁₈ glass electrical conduction and thermal character.

Helbert et al., SPIE Vol. 333 Submicron Lithography (1982): this publication generally relates to, inter alia, hybrid ultragraphic process using both electron beam and conventional optical exposure within the same device level with a photoresist.

Hilt, dissertation (1999): this publication generally relates to, inter alia, stability of chalcogenides such as Ge_xSe_{1-x} with Ag doping by photodissolution and thermal diffusion.

Hirose et al., Phys. Stat. Sol. (1980): this publication generally relates to, inter alia, switch and memory phenomena in amorphous As₂S₃ with photo-doped Ag, including new mechanism, electrical reliability, rapid memory performance, thermal characteristics and durability.

Hirose and Hirose, J. Appl. Phys. 47 (1976) 2767-2772: this document generally relates to, inter alia, Ag photodoped As₂S₃, polarized switching, and dendrite formation.

Holmquist et al., 62 J. Amer. Ceram. Soc., No. 3-4 (March-April 1979): this publication generally relates to, inter alia, reactions and diffusion of Ag in arsenic chalcogenide glass below the glass transition temperature, including solubility information and concentration dependence of Ag diffusion in these glasses.

Hong and Speyer, J. Non-Cryst. Solids 116 (1990) 191-200: this document generally relates to, inter alia, Cd-Ge-As glass with Ag contacts.

Hosokawa, J. Optoelectronics and Advanced Materials 3 (2001) 199-214: this document generally relates to, inter alia, x-ray scattering experiments on glassy $\text{Ge}_x\text{Se}_{1-x}$.

Hu, et al., J. Non-Cryst. Solids 227-230 (1998) 1187-1191: this document generally relates to, inter alia, a-Si:H with Cr and V electrodes.

Hu, et al., Phil. Mag. B. 74 (1996) 37-50: this document generally relates to, inter alia, a-Si:H glasses doped with Cr and analogue memory.

Hu, et al., Phil. Mag. B 80 (January 1, 2000) 29-43: this document generally relates to, inter alia, a-Si:H films doped with Cr-p+.

Huggett et al., 42 Appl. Phys. Lett., No. 7 (April 1983): this publication generally relates to, inter alia, reactive sputter etching to develop silver-sensitized $\text{Ge}_x\text{Se}_{1-x}$ photoresist.

Iizima, et al., Solid State Comm. 8 (1970) 153-155: this document generally relates to, inter alia, switching and memory effects in As-Te-I^{1,2} and As-Te-Ge-Si³ glass systems. Thermal breakdown is proposed switching effect.

Ishikawa and Kikuchi, J. Non-Cryst. Solids 35 & 36 (1980) 1061-1066: this document generally relates to, inter alia, Ge_2S_2 films with Ag photodissolved therein.

*Iyetomi, et al., J. Non-Cryst. Solids 262 (February 2000) 135-142: this document generally relates to, inter alia, Ag/Ge/Se glasses as a composite of GeSe_2 and Ag_2Se (a fast ion conductor) and polarizability of Se ions.

Jones and Collins, Thin Solid Films 40 (1977) L15-L18: this document generally relates to, inter alia, switching in Se films and switching back with reverse pulse.

Joullie and Marucchi, Phys. Stat. Sol. (a) 13 (1972) K105-K109: this document generally relates to, inter alia, As_2Se_7 glass.

Joullie and Marucchi, Mat. Res. Bull. 8 (1973) 433-442: this document generally relates to, inter alia, As_2Se_5 film conduction and switching.

Kaplan and Adler, J. Non-Cryst. Solids 8-10 (1972) 538-543: this document generally relates to, inter alia, thermal effects on semiconductor switching.

Kawaguchi et al., 164-166 J. Non-Cryst. Solids (1993): this publication generally relates to, inter alia, deposition mechanism of Ag particles on Ag-rich Ag-As-S glass from a view-point of electrical effects.

*Kawaguchi, et al., J. Appl. Phys. 79 (1996) 9096-9104: this document generally relates to, inter alia, Ag-rich chalcogenide glass, Ge_3S_7 -Ag and $\text{Ge}_{30}\text{Se}_{70}$ -Ag, max Ag content of 67%, graphs phase diagram, and discloses that Ag works better than Cu.

*Kawaguchi and Masui, Jpn. J. Appl. Phys. 26 (1987) 15-21: this document generally relates to, inter alia, silver photodoping of chalcogenide films, e.g., $\text{Ge}_{30}\text{Se}_{70}$ films.

*Kawasaki, et al., Solid State Ionics 123 (1999) 259-269: this document generally relates to, inter alia, the electrical properties of $\text{Ag}_x(\text{GeSe}_3)_{1-x}$, conductivity EMF measurements, glass composition, X-ray diffraction, T_g and T_c , Ag ion transport, and glass structure.

*Kluge, et al., J. Non-Cryst. Solids 124 (1990) 186-193: this document generally relates to, inter alia, photodiffusion of silver into $\text{Ge}_x\text{Se}_{100-x}$ layers, how this differs from ion beam induced diffusion, $\text{Ge}_{30}\text{Se}_{70}$ stoichiometry, Ag_2Se , and percolation threshold.

*Kolobov, J. Non-Cryst. Solids 198-200 (1996) 728-731: this document generally relates to, inter alia, p-type conductive chalcogenides, materials, and physics thereof.

*Kolobov, J. Non-Cryst. Solids 137-138 (1991) 1027-1030: this document generally relates to, inter alia, doped and undoped glass layers as a p-n junction.

*Kolobov and Elliott, Advances in Physics (1991): this publication generally relates to, inter alia, photodoping (photodiffusion/photodissolution) of amorphous chalcogenides by metals, particularly silver.

Korkinova and Andreichin, J. Non-Cryst. Solids 194 (1996) 256-259: this document generally relates to, inter alia, polarization of chalcogenide glass as depending on the materials used for electrode contacts.

*Kotkata, et al., Thin Solid Films 240 (1994) 143-146: this document generally relates to, inter alia, GeSe glass switching and film thickness, memory, current filament, chemical and mechanical switching properties, and discloses that heat treatment or aging improves switching.

*Kozicki and Mitkova, Proceedings of the XIX International Congress on Glass, Society for Glass Technology (2001): this publication generally relates to, inter alia, the physical effects of introduction of Ag into chalcogenide glasses, where introduction is by photodiffusion.

*Michael N. Kozicki, Programmable Metallization Cell Technology Description, February 18, 2000: this publication generally relates to, inter alia, programmable metallization cells (PMC) for storing memory as resistive states. The PMC cells use a chalcogenide glass region bounded by electrodes as a memory device. The chalcogenide glass can be germanium selenide. The electrodes can be an oxidizable and indifferent material. Multiple-bit cells are disclosed; relying on controlling an amount of electrodeposit. Barrier layers of metal oxides, isolation diodes, and access transistors are also disclosed.

*Michael N. Kozicki, Axon Technologies Corp. and Arizona State University, Presentation to Micron Technology, Inc., April 6, 2000: this publication generally relates to, inter alia, programmable metallization cells (PMC) for storing memory as resistive states and operating parameters for PMC devices.

*Kozicki et al., Proceedings of the 1999 Symposium on Solid State Ionic Devices (1999): this publication generally relates to, inter alia, physical and electrical characteristics of metal doped chalcogenide films (photodoped $\text{Ag}_4\text{As}_2\text{S}_3$) between

electrodes, useful in memories, configurable connections, and self-repairing interconnections.

*Kozicki et al., Superlattices and Microstructures, 27 (2000): this publication generally relates to, inter alia, solid solutions of metals (e.g., silver) in arsenic trisulfide and their physical and electrical characteristics.

*Kozicki et al., Microelectronic Engineering, vol. 63/1-3 (2002): this publication generally relates to, inter alia, the photodiffusion of Ag into germanium selenide glass films, the amount of Ag that can be incorporated in to such a film by photodiffusion, and the characteristics of the resulting doped films.

Lakshminarayan, et al., J. Instrn. Electronics & Telecom. Engrs. 27 (1981) 16-19: this document generally relates to, inter alia, tellurium-containing chalcogenide glasses.

Lal and Goyal, Indian Journal of Pure & Appl. Phys. 29 (1991) 303-304: this document generally relates to, inter alia, theory on chalcogenide switching.

*Leimer et al., Phys. Stat. Sol. (a) 29 (1975) K129-K132: this document generally relates to, inter alia, germanium selenide glass polarization behavior, e.g., inductive and capacitive components.

*Leung, et al., Appl. Phys. Lett. 46 (1985) 543-545: this document generally relates to, inter alia, photoinduced diffusion of Ag into $\text{Ge}_x\text{Se}_{1-x}$ and techniques for same.

Matsushita, et al., Jap. J. Appl. Phys. 11 (1972) 1657-1662: this document generally relates to, inter alia, Se-SnO₂ film switching and reversibility.

Matsushita, et al., Jpn. J. Appl. Phys. 11 (1972) 606: this document generally relates to, inter alia, polarized memory effect in Se films.

Mazurier, et al., Journal de Physique IV 2 (1992) C2-185 - C2-188: this document generally relates to, inter alia, Te-based glasses.

McHardy et al., 20 J. Phys. C.: Solid State Phys. (1987): this publication generally relates to, inter alia, sensitivity and high resolution of metals in amorphous chalcogenides by electron and UV radiation.

Messoussi, et al., Mat. Chem. And Phys. 28 (1991) 253-258: this document generally relates to, inter alia, selenium films and Bi electrodes.

*Mitkova and Boolchand, J. Non-Cryst. Solids 240 (1998) 1-21: this document generally relates to, inter alia, the analysis of Group IV and V chalcogenides.

*Mitkova and Kozicki, J. Non-Cryst. Solids 299-302 (May 14, 2002) 1023-1027: this document generally relates to, inter alia, photodissolution of Ag into Se-rich Ge-Se glasses for use in memory devices. The information disclosed in this reference was available to and known by the inventors prior to the filing of the application.

*Mitkova, et al., Phys. Rev. Lett. 83 (1999) 3848-3851: this document generally relates to, inter alia, Ag doped chalcogenides, $\text{Ge}_{20}\text{Se}_{80}$ stoichiometry is disclosed, Se rich glasses, Ge rich glasses, stoichiometric glasses, and presence of Ag_2Se .

*Miyatani, J. Phys. Soc. Japan 34 (1973) 423-432: this document generally relates to, inter alia, electrical and ionic properties of solid solutions (e.g., doped glass), polarization, conductivity, Ag_2Se and Cu_2Se .

Miyatani, J. Phys. Soc. Japan 13 (1958) 317: this document generally relates to, inter alia, experiments regarding the electronic conductivity, ionic conductivity, hall constant, thermoelectric power, and Nernst coefficient of Ag_2Se as function of the e.m.f., E, the galvanic cell, or the deviation from stoichiometric composition.

*Miyatani, J. Phys. Soc. Japan 14 (1959) 996-1002: this document generally relates to, inter alia, Ag_2Te and Ag_2Se ion conduction and the chemical potential of silver ions.

Mott, J. Non-Cryst. Sol. 1 (1968) 1-17: this document generally relates to, inter alia, glasses with vanadium or iron.

*Nakayama, et al., Jpn. J. Appl. Phys. 32 (1993) 564-569: this document generally relates to, inter alia, electrically erasable nonvolatile memories in chalcogenide films of $\text{As}_x\text{Sb}_y\text{Te}_z$, flash evaporative deposition techniques, a high set-voltage compared to read-voltage, V_t creates a "filament," and refresh-type pulse.

*Nakayama, et al., Jpn. J. Appl. Phys. 39 (November 15, 2000) 6157-6161: this document generally relates to, inter alia, phase transition random access memory (PRAM) made of chalcogenide glass.

*Nang et al., Jap. J. App. Phys. 15 (1976) 849-853: this document generally relates to, inter alia, $\text{Ge}_x\text{Se}_{1-x}$ electrical and optical properties; it also discloses $\text{Ge}_{.80}\text{Se}_{.20}$, $\text{Ge}_{.60}\text{Se}_{.40}$, and $\text{Ge}_{.50}\text{Se}_{.50}$.

Narayanan, et al., Phys. Rev. B 54 (1996) 4413-4415: this document generally relates to, inter alia, chalcogenide glass switching as thermally originated.

*Neale and Aseltine, , IEEE Transactions On Electron Dev. Ed-20 (1973) 195-209: this document generally relates to, inter alia, read mostly memories with chalcogenides (e.g., Ge, Te), also discloses "floating gate," and material combinations including Ge and Se.

Ovshinsky and Fritzsche, Metallurgical Transactions 2 (1971) 641-645: this document generally relates to, inter alia, reversible changes in amorphous Si, Be, and B using a laser to write and erase.

Ovshinsky, Phys. Rev. Lett. 21 (1968) 1450-1453: this document generally relates to, inter alia, rapid and reversible resistive switching by electric field in amorphous semiconductors.

Owen, et al., IEE Proc. 129 (1982) 51-54: this document generally relates to, inter alia, a-Si:H, gold or aluminum dots and silver paste.

Owen, et al., Phil. Mag. B 52 (1985) 347-362: this document generally relates to, inter alia, photoinduced chalcogenide effects (As_2S_3) both reversible and irreversible.

*Owen, et al., Int. J. Electronics 73 (1992) 897-906: this document generally relates to, inter alia, threshold and memory switching a-Si:H ion conductor, polarity-dependant digital memory, analogue memory, and device operation dependency on metal contacts.

Owen et al., Nanostructure Physics and Fabrication (1989): this publication generally relates to, inter alia, photo-induced structural or physico-chemical changes of amorphous chalcogenides when exposed to light/irradiation, affecting chemical solubility.

Pearson and Miller, App. Phys. Lett. 14 (1969) 280-282: this document generally relates to, inter alia, glass diodes.

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